



- Multiplication of Dislocations
  - Nucleation
  - Glide Sources (Single-Arm, Two-Arm)
  - Cross-Slip Sources
  - Climb Sources
  - Helical Source
  - Other Sources of Dislocations

# Nucleation

- In Ch. 3d, we have seen that **vacancies spontaneously form at finite temperature** due to rather low formation enthalpy and gain in entropy by a configurational contribution.
- In Ch. 4c, we have seen that the **formation enthalpy of dislocation lines is orders of magnitude larger**. Hence, there is nothing like an equilibrium density.
- At 0 K (no thermal fluctuations), the critical stress to form a dislocation loop is in the order of  $\tau_c \approx \frac{G}{10}$  **at a critical size of the loop of  $3b$  (same meaning of critical as in typical nucleation theory for other subjects)**. If smaller **stresses in the order of ordinary yield strength of metals** are considered, the **critical sizes are in the order of several hundred  $b$** . Even increasing temperatures, cannot sufficiently support the nucleation of loops.

# Single-Arm Sources

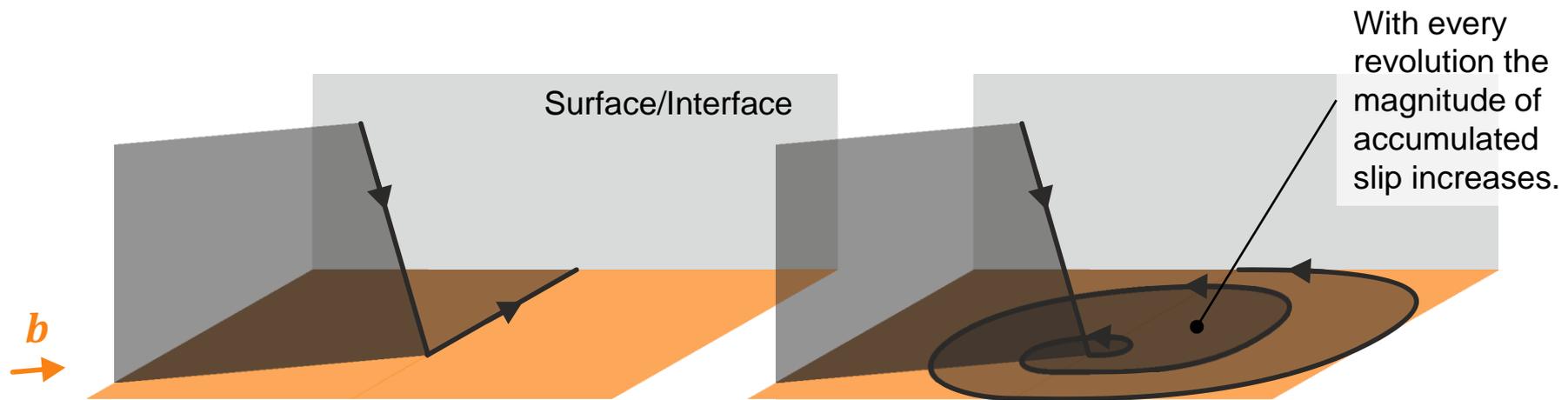
- In Ch. 4c, we have seen that a **glissile dislocation segment can rotate** about a sessile segment.
- **By every revolution**, the **slip step** on the surface of the crystal **increases by one Burgers vector**.
- The **glissile segment tends to form a spiral** due to the relaxed structure of the dislocation at the surface/discontinuity of the crystal. The length of the dislocation line increases:



*Single-arm glide source: initial state and after several revolutions*

# Single-Arm Sources

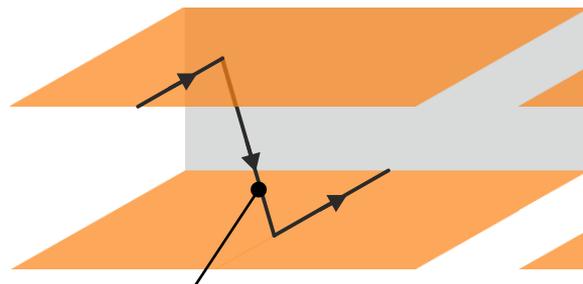
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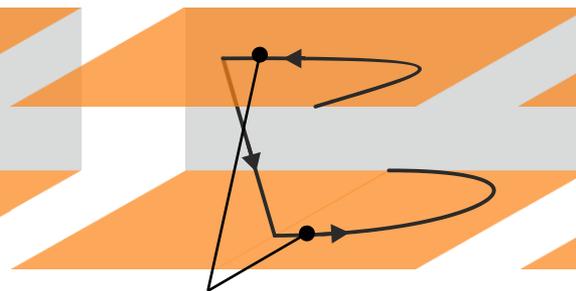
*Slipped regions of the same.*

# Single-Arm Sources

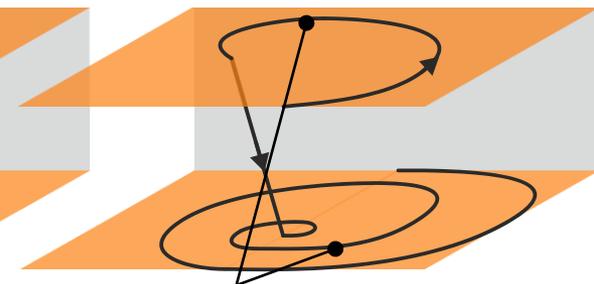
- In case of a formation of the single arm by dislocation intersection (**jog**), the **stress for passing has to be considered**. As seen in Ch. 4d, the stress for passing by significantly increases for closely spaced dislocations. Hence, many intersection processes have to produce sufficiently large jogs:



jog of  $l$  in length

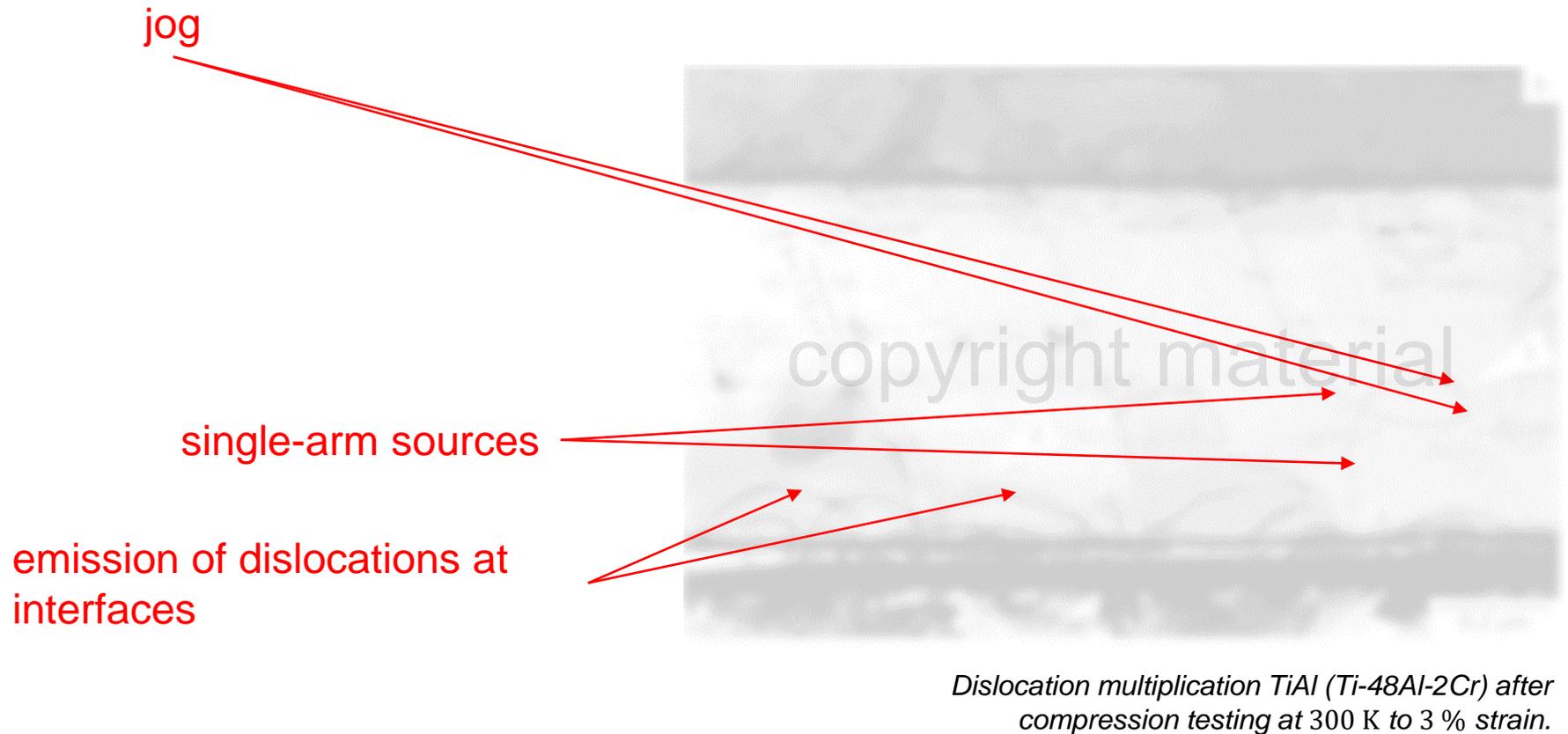


formation of an extended dipole (anti-parallel line sense!) in case of a blocked source



in case the stress is sufficient for passing, the source can be activated

# Single-Arm Sources



F. Appel et al.: "Recent Progress in the Development of Gamma Titanium Aluminide Alloys" in Adv. Eng. Mat. 2 (2000) 699-720

# Single-Arm Sources

- Glide component of the interaction force between two anti-parallel edge dislocations (Ch. 4d):

$$\frac{F_x}{L} = - \frac{G b^2}{2\pi (1 - \nu)} \frac{x \cdot (x^2 - y^2)}{(x^2 + y^2)^2}$$

- Maximum force:

$$\frac{F_x^{\max}}{L} = \frac{G b^2}{8\pi (1 - \nu)} \frac{1}{l}$$

- Glide component of the interaction force between two anti-parallel screw dislocations (Ch. 4d):

$$\frac{F_x}{L} = - \frac{G b^2}{2\pi} \frac{x}{x^2 + y^2}$$

- Maximum force:

$$\frac{F_x^{\max}}{L} = \frac{G b^2}{4\pi} \frac{1}{l}$$

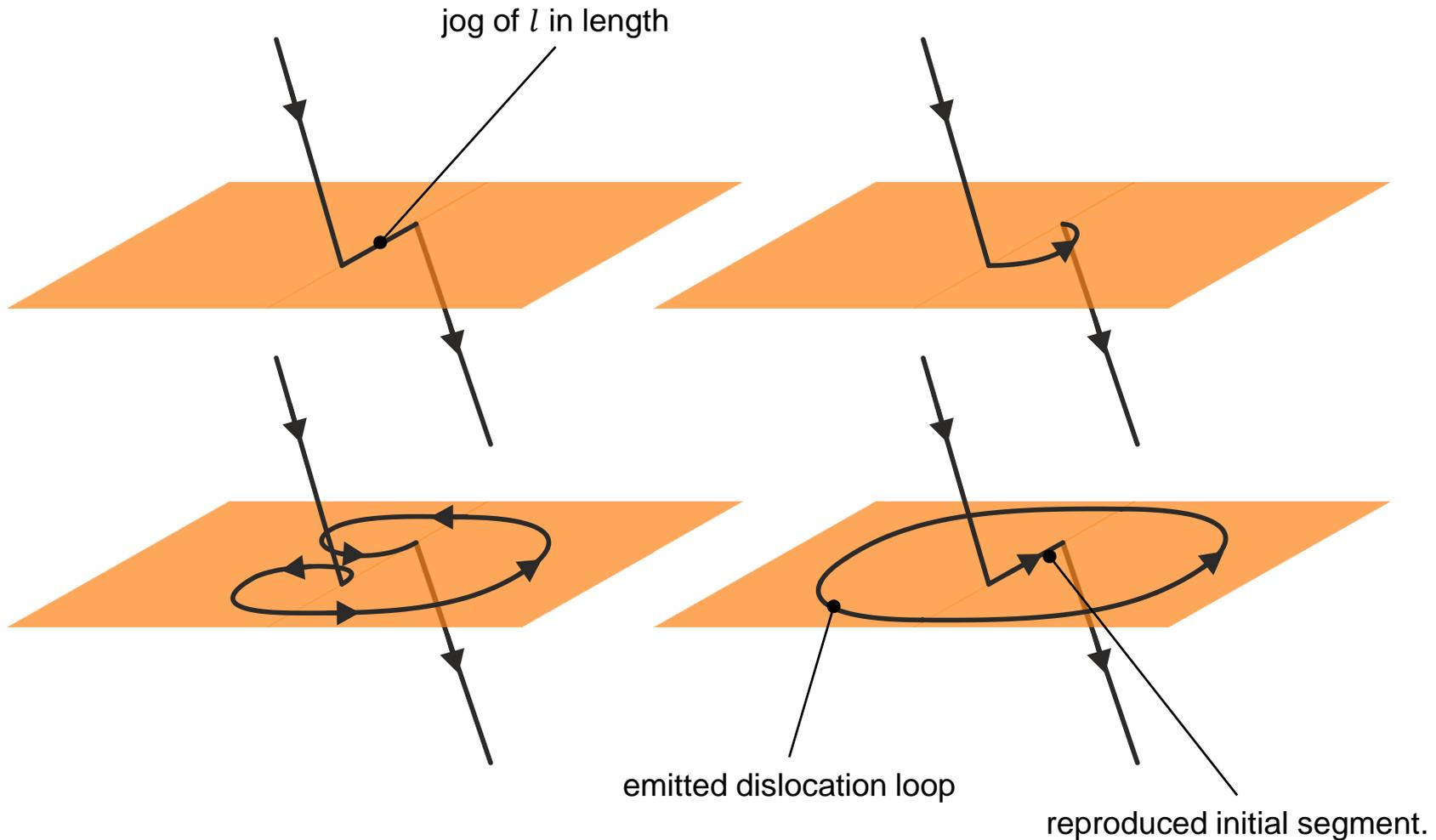
# Single-Arm Sources

- The **critical stress for the activation of the source** is:  $\tau_c b = \frac{F_x^{\max}}{L}$ .
- Hence, for the single-arm source  $\tau_c = \left( \frac{G b}{8\pi(1-\nu)} \dots \frac{G b}{4\pi} \right) \frac{1}{l}$  follows.
- For **reasonable yield strengths** of roughly  $\tau \approx \frac{G}{1000} \dots \frac{G}{100}$ , the jog must be of  $l \approx 6 \dots 60 b$  **or**  $8 \dots 80 b$  **in length** for edge or screw dislocations, respectively.
- The lower bound is realistic for jog-forming intersections.

## Two-Arm Source: Frank-Read Source

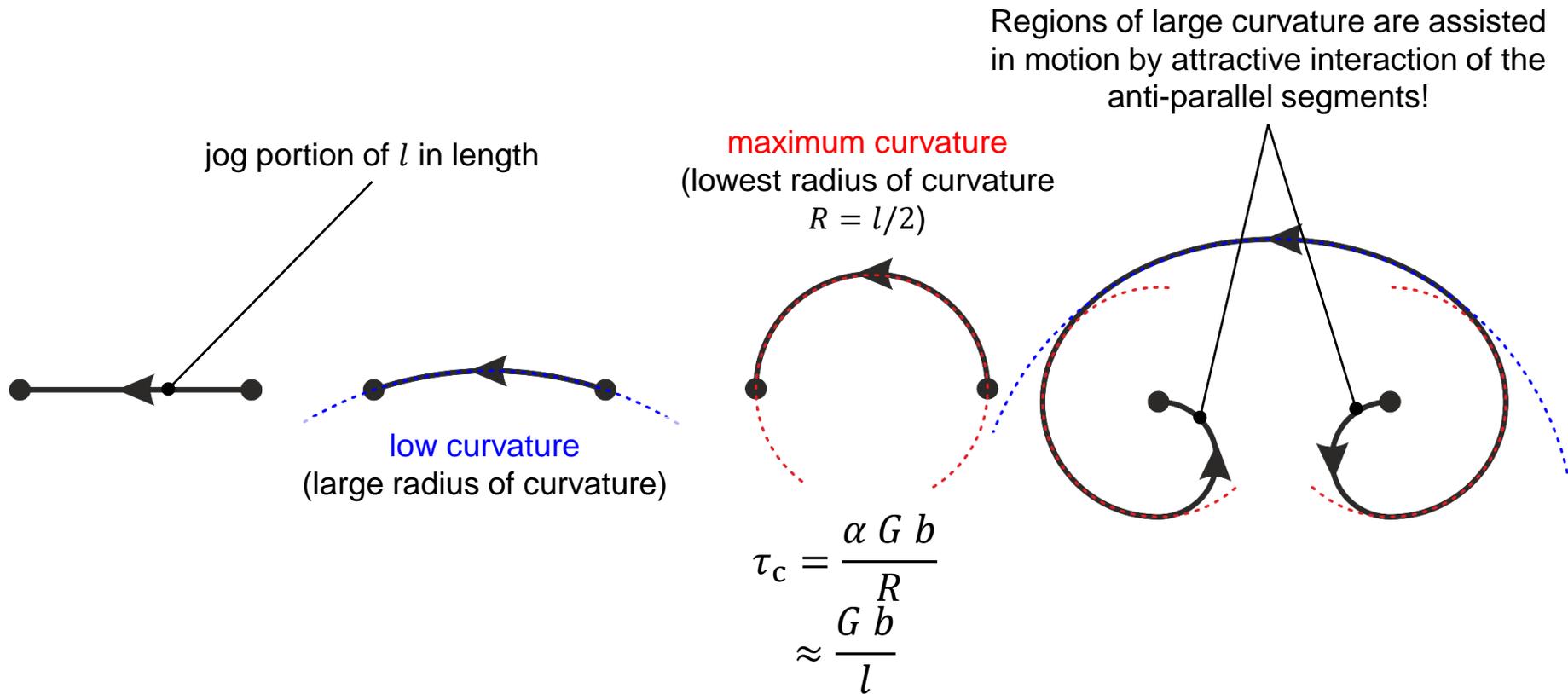
- By assuming **another pinning point**, the single-arm source converts into a **two-arm source**, well-known as the **Frank-Read source**.
- Due to the **rotation** about the pinning points, the **initially straight dislocation line transforms into an arc**.
- The **back stress** by the arcs increases **until the semi-circle configuration** is achieved with  $\tau_c = \frac{G b}{l}$  **at**  $R = \frac{l}{2}$ . Every other configuration needs lower stress to be achieved.
- **By spiraling around, anti-parallel dislocation segments meet and annihilate**. A **new dislocation loop around the original dislocation segment** is formed. The **process continues** in the same way.
- Due to the large size of the loops, the loops expand under the applied stress.
- Any pile-up of the dislocation loops results in back stress and potential de-activation of the source.

# Two-Arm Source: Frank-Read Source



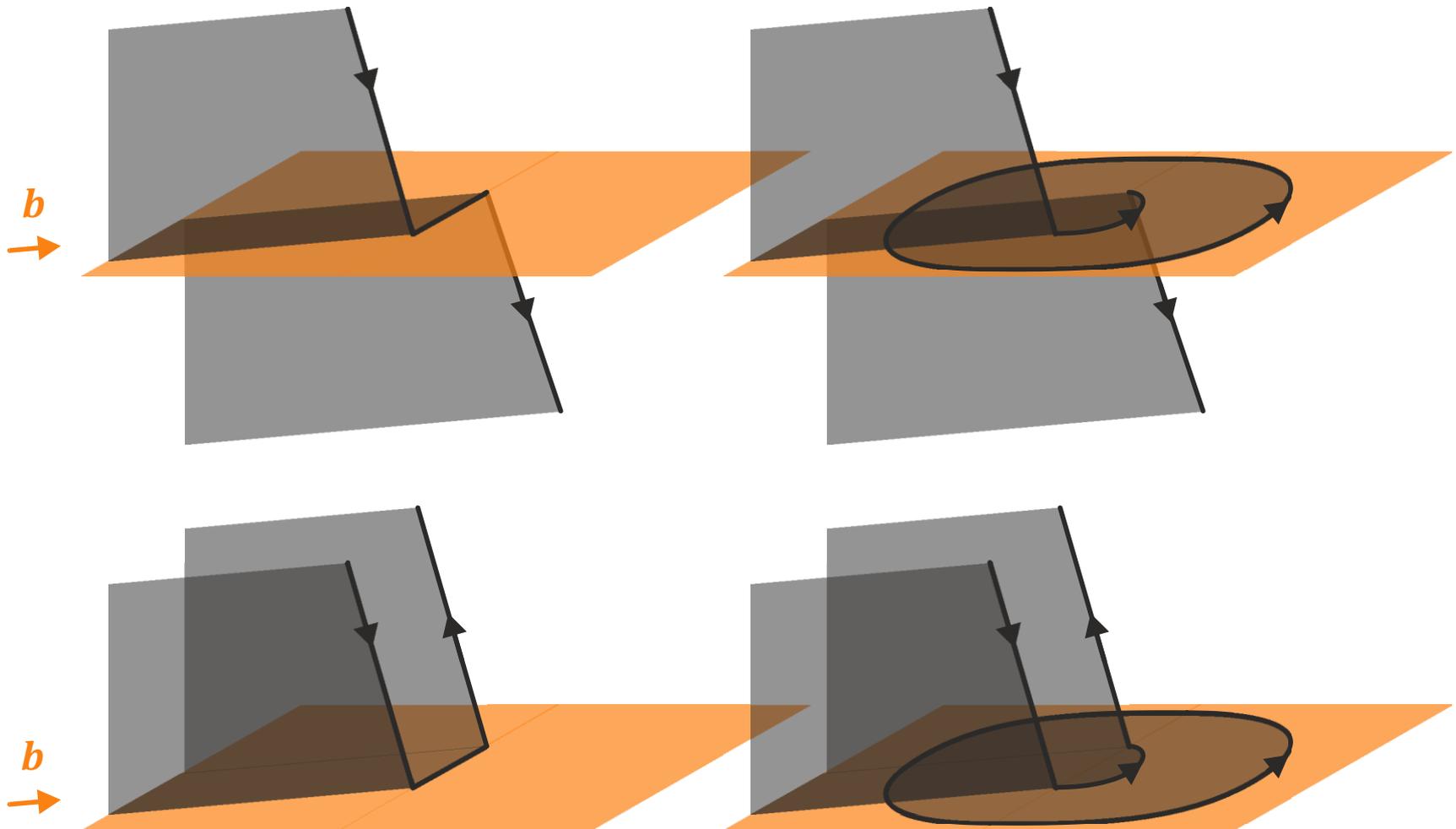
*Two-arm source: various states.*

# Two-Arm Source: Frank-Read Source



*Two-arm source: various states with tangent circles to visualize curvature.*

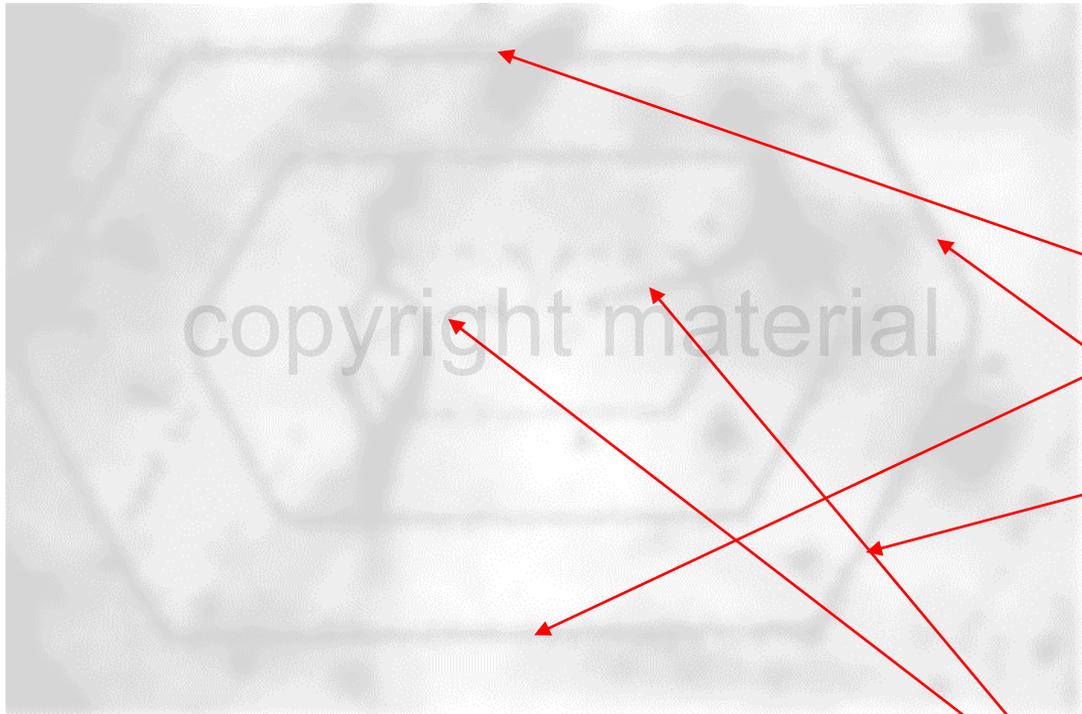
# Two-Arm Source: Frank-Read Source



*Slipped regions of the same: (upper part) Z shape, (lower part) U shape.*

# Two-Arm Source: Frank-Read Source

$$\longrightarrow \mathbf{b} = \frac{1}{2} [1\bar{1}0]$$



(111)

screw segments

60°-segments along  
[10 $\bar{1}$ ] and [01 $\bar{1}$ ]

*Frank-Read source in Si. Decoration by Cu atoms.*

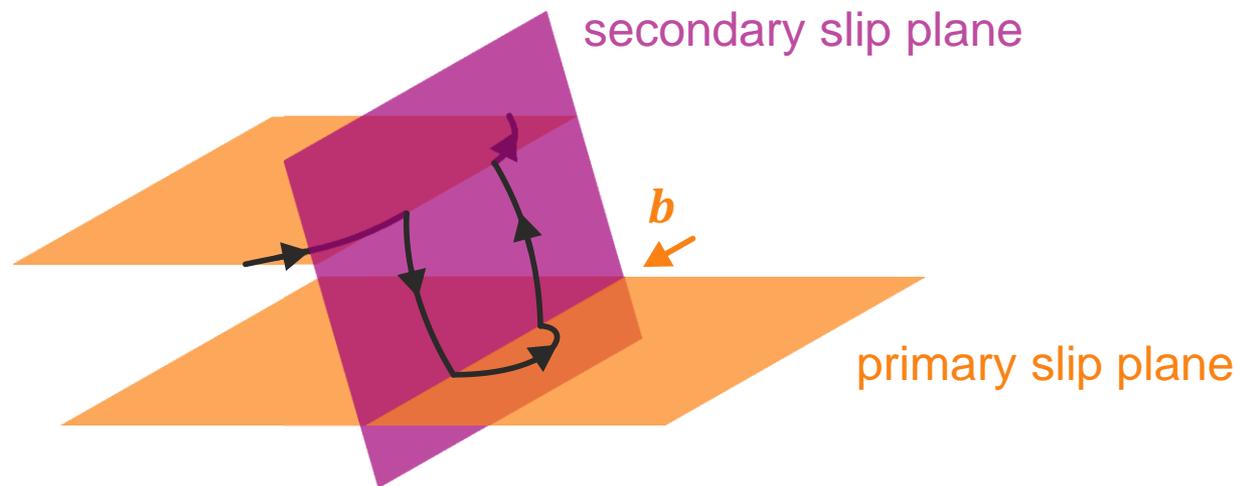
two segments not in the slip plane (and out-of-focus)

D. Hull, D. J. Bacon: "Introduction to Dislocations", Amsterdam, etc.: Elsevier (2011)

# Two-Arm Source: Frank-Read Source

- Assuming again stresses in the order of  $\tau \approx \frac{G}{1000} \dots \frac{G}{100}$ , the segment enclosed by the pinning points must be of  $l \approx 10^3 \dots 10^2 b$  in length.
- For the **Z shape**, the segment could be a result of intersection processes. It would be **a jog**. Since every intersection process only leads to an increase of  $1b$ , a total length of  $10^3 \dots 10^2 b$  is only reasonable when another source on the same slip plane is already operating.
- The **U shape** might **originate from cross-slip** processes when the points of slip plane change are efficiently pinned (for example by dissociation). This process is conceivable.

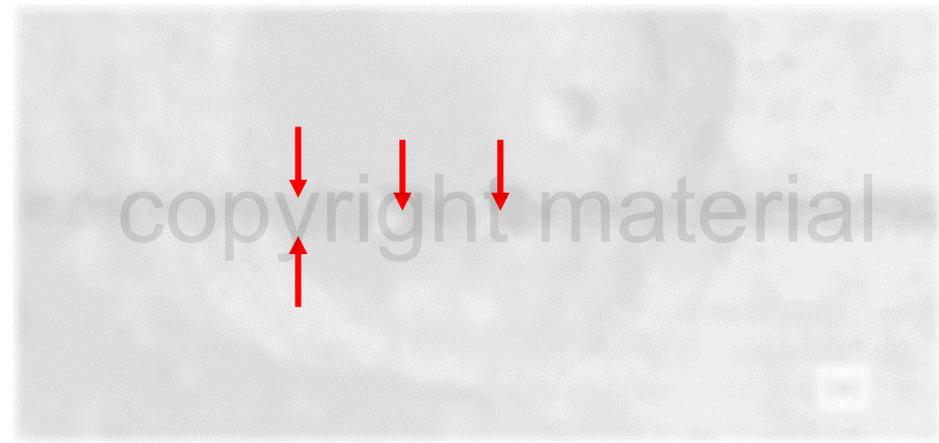
# Two-Arm Source: Frank-Read Source



*Two-arm source by cross-slip.*

# Significance in Experimental Results

- The increase of the width of deformation bands during plastic deformation indicates the significance of cross-slip in dislocation multiplication.
- The deformation bands gradually increase their thickness during plastic deformation by cross-slip.

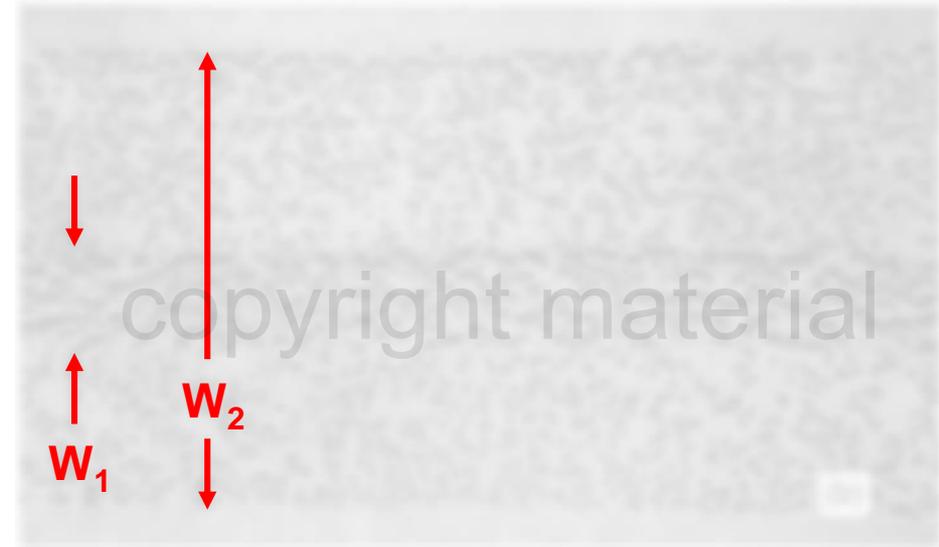


*Development of a single dislocation segment (large etch pits) to a deformation band (multiple small etch pits) by cross-slip and dislocation multiplication in LiF.*

D. Hull, D. J. Bacon: "Introduction to Dislocations", Amsterdam, etc.: Elsevier (2011)

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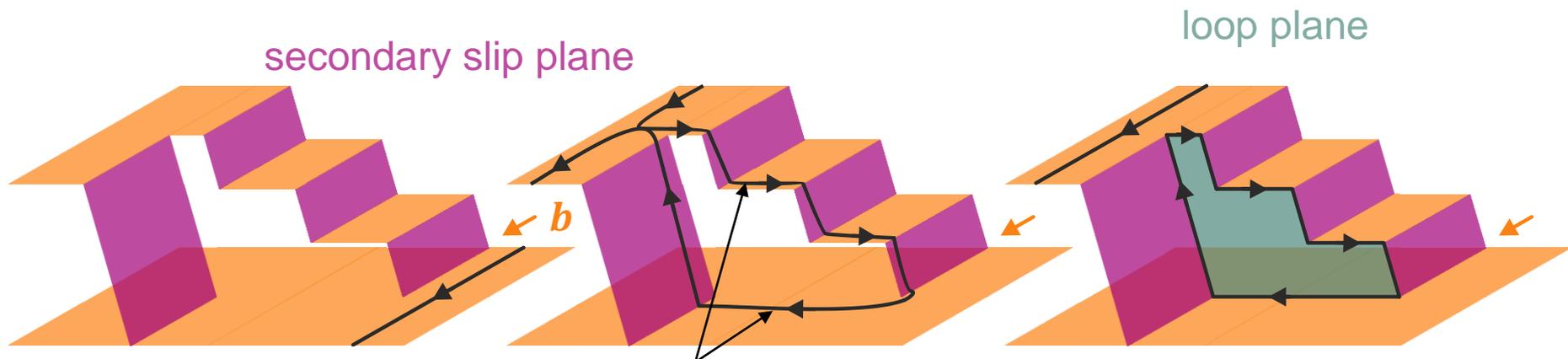


*Development of deformation band thickness in LiF.*

D. Hull, D. J. Bacon: "Introduction to Dislocations", Amsterdam, etc.: Elsevier (2011)

# Loop Formation by Cross Slip

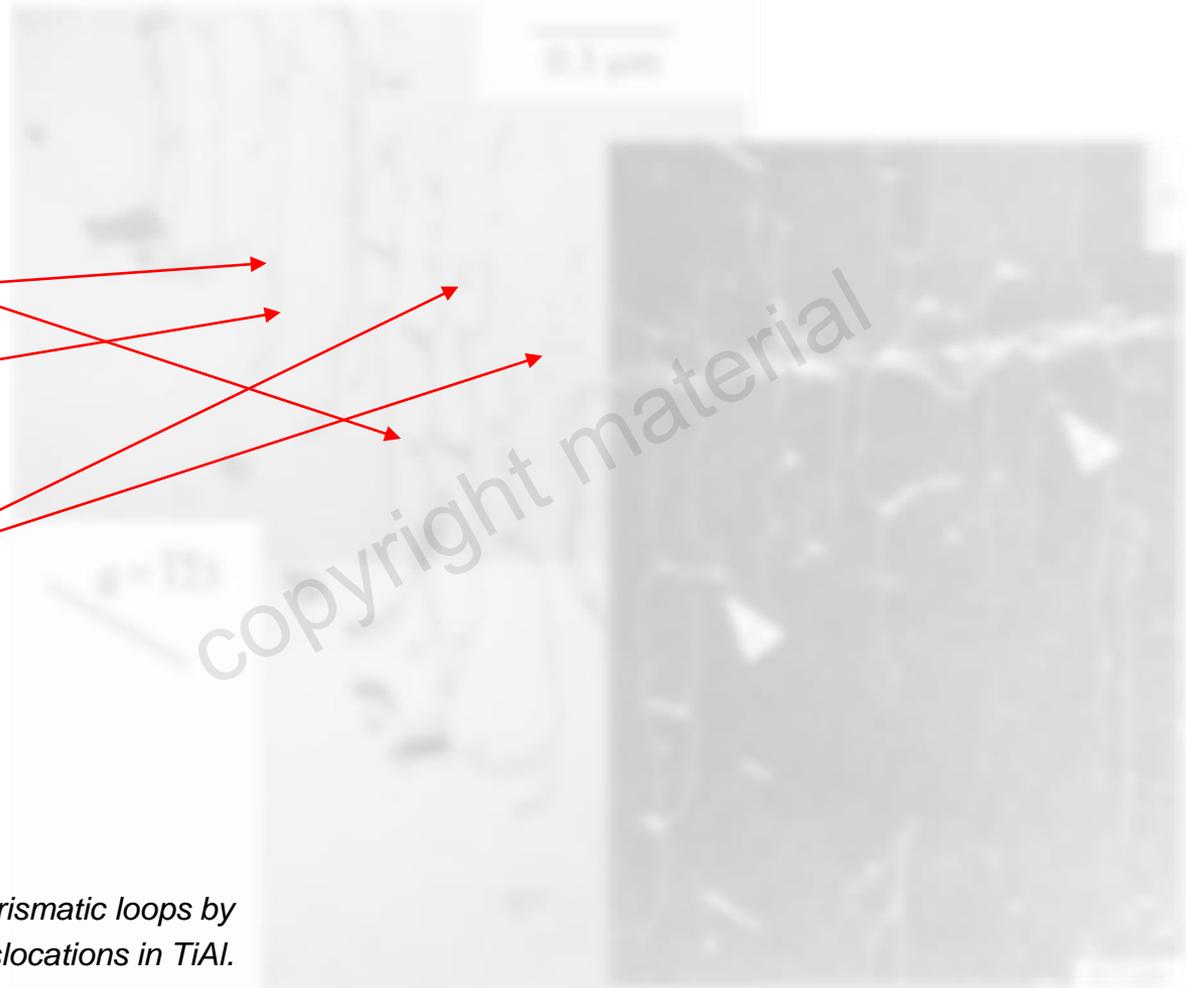
- In materials with **high Peierls barriers and preferred screw character of dislocations** (A2 metals and intermetallics), **segment-wise cross-slip** can lead to the **formation of prismatic loops** (see Ch. 3a, only edge character along the dislocation loop).
- It is also observed in particle strengthened materials, since the induced cross-slip by the obstacle can lead to this configuration (one kind of bypassing the particle, Orowan mechanism).



Note the dislocations are of anti-parallel sense: “extended dipoles”.

*Formation of prismatic loops by segment-wise cross-slip.*

# Loop Formation by Cross Slip



*Formation of extended dipoles and prismatic loops by cross-slip of  $\frac{1}{2}\langle 110 \rangle$  screw dislocations in TiAl.*

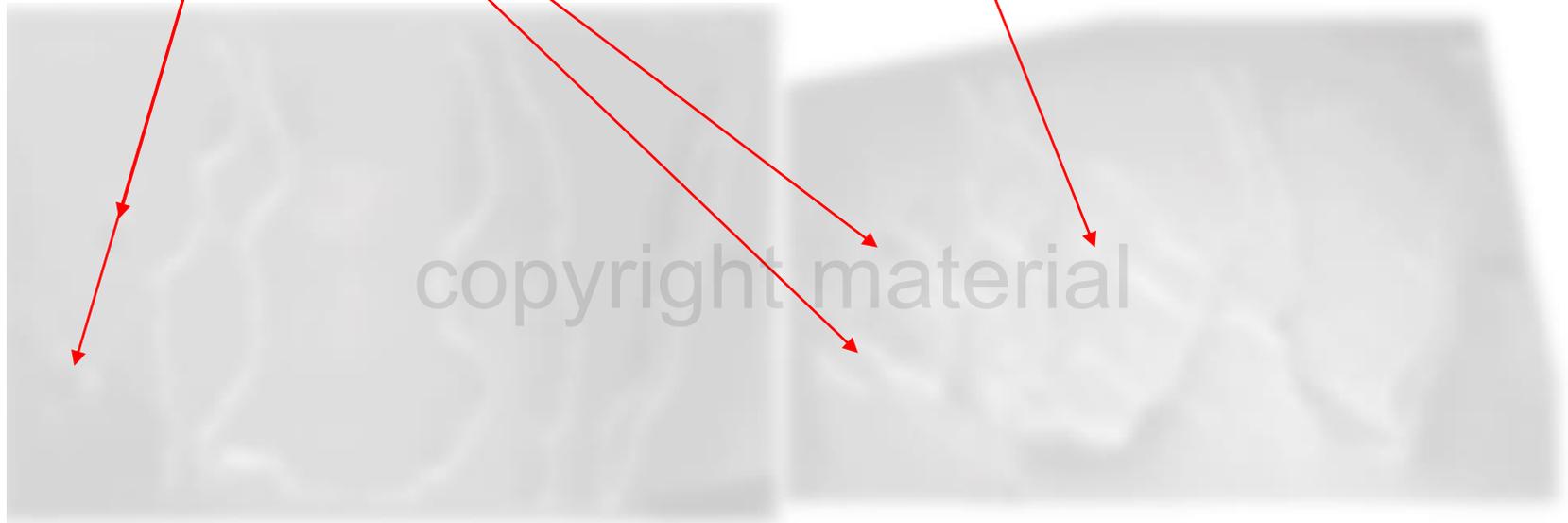
D. Caillard , M. Legros & A. Couret: "Extrinsic obstacles and loop formation in deformed metals and alloys" in Phil. Mag. 93 (2013) 203-221  
 F. Appel et al.: "Recent Progress in the Development of Gamma Titanium Aluminide Alloys" in Adv. Eng. Mat. 2 (2000) 699-720

# Loop Formation by Cross Slip

same positions

loops

*a + c super dislocations on pyramidal planes of  $Ti_3Al$  during an in-situ deformation experiment: (left) initial state, (right) after plastic deformation.*

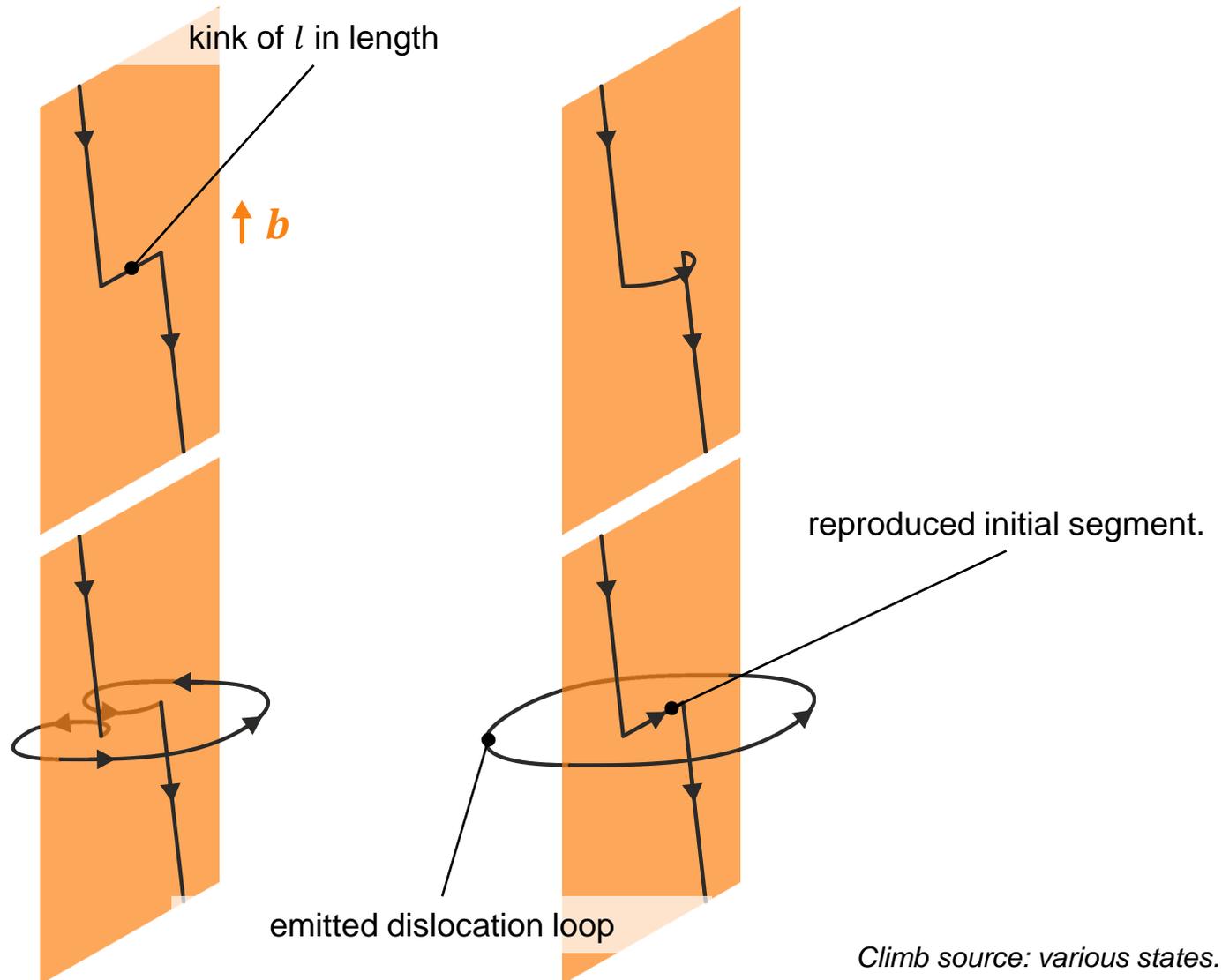


D. Caillard , M. Legros & A. Couret: "Extrinsic obstacles and loop formation in deformed metals and alloys" in Phil. Mag. 93 (2013) 203-221

# Climb Source: Bardeen-Herring Source

- For the activation of climb sources, a **supersaturation in vacancies** is necessary. This can be achieved for example **by quenching from higher temperatures or irradiation**.
- Similar to what is observed for the Frank-Read source, the critical point is the semi-circle configuration  $R = \frac{l}{2}$ . The amount of supersaturation can, therefore, be estimated by  $\ln\left(\frac{x}{x_0}\right) = \frac{G b \Omega}{l k_B T}$  (see Ch. 3c for the chemical force on dislocation lines).
- Since we assume a climb process, the **Z shape** is not formed from a jog but from a **kink**.

# Climb Source: Bardeen-Herring Source



# Climb Source: Bardeen-Herring Source

- Hence,  $\Omega \approx b^3$  at  $T = 300$  K and with  $G \approx 25$  GPa as well as  $b \approx 2.9$  Å lead to (Al):

$$l \approx \frac{150}{\ln\left(\frac{x}{x_0}\right)} b$$

- A supersaturation of only  $\ln\left(\frac{x}{x_0}\right) = 25$  leads to a small kink of only  $l \approx 6 b$ .
- Compare this with following quenching process

- $x_0 = e^{\frac{\Delta S_V^P}{k_B}} e^{-\frac{\Delta H_V^F}{k_B T}}$  with  $\Delta S_V^P = 2.4 k_B$ ,  $\Delta H_V^F = 1.27$  eV (again Al)
- yields  $x_0 = 5 \cdot 10^{-21}$  and  $x = 2 \cdot 10^{-10}$  at  $T = 300$  and  $600$  K, respectively
- **the supersaturation for quenching from 600 to 300 K is then**

$$\ln\left(\frac{x}{x_0}\right) \approx 25$$

# Climb Source: Bardeen-Herring Source

- In many **intermetallic materials**, **anomalies of vacancies concentration** exist (note that there are thermal, constitutional, and structural vacancies possible)
- Due to the small excess vacancy concentration for activation of the climb source, climb sources are frequently found.

Bardeen-Herring source

growth of prismatic loops



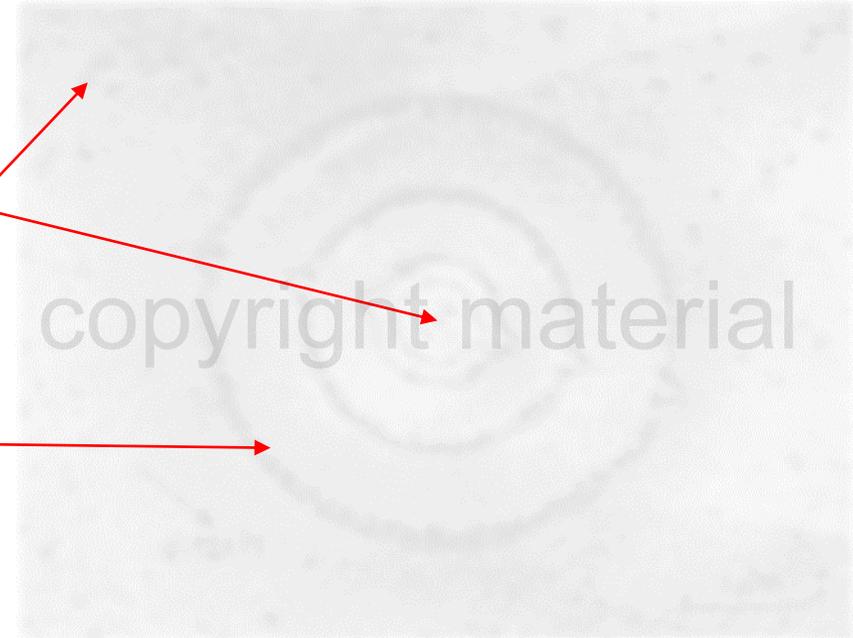
*B-H source and growth of prismatic loops by vacancy agglomeration in TiAl at 820 K.*

F. Appel et al.: "Recent Progress in the Development of Gamma Titanium Aluminide Alloys" in Adv. Eng. Mat. 2 (2000) 699-720

# Climb Source: Bardeen-Herring Source

Bardeen-Herring source

many small prismatic loops



The vacancy agglomeration of the small loops retards the expansion of large loops. At the bulge, less small loops are formed due to cross-slip and, hence, the larger loops can expand further. Note that not all loops are visible for this diffraction condition!

*Prismatic loops in an Al-4Cu single crystal subsequent to 793 K/2 h/quenching and ageing at 266 K with compression load along [011] at 30 MPa. Viewing direction is along [110].*

A. Sato, Y. Sugisaki & T. Mori: "Observation of dislocation sources in a quenched and stress-aged Al-4 wt% Cu alloy single crystal" in *Phil. Mag.* 51 (1985) 133-143

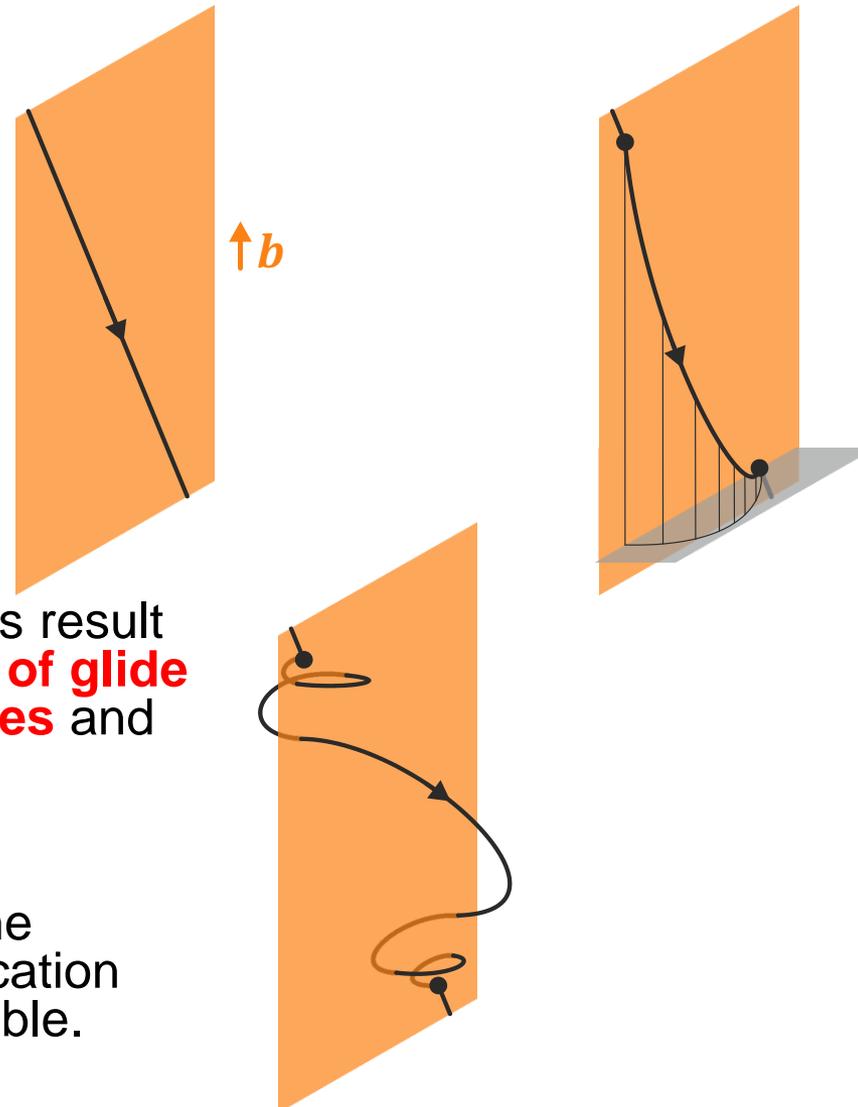
# Climb Source: Bardeen-Herring Source



*Prismatic loops in Al-3.5Mg subsequent to quenching from 550 °C.*

D. Hull, D. J. Bacon: "Introduction to Dislocations", Amsterdam, etc.: Elsevier (2011)

# Helical Source



- Mixed dislocations result in **combinations of glide and climb sources** and the **formation of spirals/helices**.
- Under certain circumstances, the emission of dislocation loops is still possible.

*Helical source: various states.*

# Helical Source

helix



*Formation of the helix during in-situ heating in the TEM after deformation at room temperature.*

F. Appel et al.: "Recent Progress in the Development of Gamma Titanium Aluminide Alloys" in Adv. Eng. Mat. 2 (2000) 699-720

# Other Sources

- **Heterogonous nucleation at interfaces** is also an important contribution to dislocation multiplication.
- Following issues during assessment have to be considered:
  - Interfaces are usually points of stress concentrations. Hence, stresses might be significantly higher than expected from external load.
  - High interface density leads to high nucleation rates. In contrast very narrow interface spacing can restrict the free motion of the arms of dislocation sources and block the dislocation multiplication.

# Summary

- **Dislocation do not form spontaneously.**
- **Dislocations nucleate at surfaces and interfaces** in heterogonous materials.
- Dislocations sources can be grouped by the major contribution to dislocation motion: **glide, cross-slip and climb**. In general, **single-arm** and **two-arm** sources are possible.